

PUBLICATION LIST

JEN-INN CHYI (蔡振瀛)

(B) CONFERENCE PAPER

International conferences:

1. J. Klem, J.-I. Chyi, H. Morkoc, Y. Ihm, and N. Otsuka, "Electrical Characteristics of MBE-grown GaAsSb on InP and Correlation with Film Microstructure", SPIE Proceeding, Vol.877, pp.35, 1988.
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3. D. Huang, J.-I. Chyi, S. Kalem, and H. Morkoc, "Excitonic Absorption in P-type Modulation Doped GaAs Quantum Wells", the Meeting of the American Physical society, St. Louis, Missouri, 1988.
4. J.-I. Chyi, D. Biswas, S. Lyer, N. Kumar, H. Morkoc, R. Bean, K. Zanio, R. Grober, and D. Drew, "MBE Growth and Characterization of InSb on Si", 9th NAMBE Workshop, West Lafayette, Indiana, 1988.
5. C. J. Kiely, J.-I. Chyi, A. Rockett, and H. Morkoc, "High Resolution Electron Microscopy Studies of MBE Grown InSb Layers on GaAs", MRS Symposium Proceedings Series, Vol.139, Edited W. Krakow, F.A. Ponce, and D.J. Smith. 1989.
6. J.-I. Chyi, J. Chen, N. Kumar, C. Kiely, C. K. Peng, A. Rockett, and H. Morkoc, "Low Resistance Nonalloyed Ohmic Contacts on P-type GaAs Using GaSb/GaAs Strained-Layer Superlattices", Electronic Materials Conference, Cambridge, Massachusetts, 1989.
7. J. Chen, G.B. Gao, D. Huang, J.-I. Chyi, M. S. Unlu, and H. Morkoc, "Light Emission from the GaAs/AeGaAs HBT Collector Junction at Breakdown", 47th Device Research Conference, Cambridge, Massachusetts, 1989.
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9. M. S. Unlu, J.-I. Chyi, K. Kishino, J. Reed, S.N. Mohammad, and H. Morkoc, "Gain and Spectral Response of MBE-grown AlGaAs/GaAs Heterojunction Bipolar Phototransistor with an Intermediate InGaAs Layer in the Collector", CLEO, Anaheim, 1990.
10. M.-T. Yang, R.-M. Lin, Y.-J. Chan, J.-L. Shieh, and J.-I. Chyi, "Thermal Stability of Strained AlGaAs/In_xGa_{1-x}As (0.15<x<0.25) Doped-Channel Structures", 20th Intl. Symposium on GaAs and Related Compounds, Freiburg, Germany, 1993.
11. J.-I. Chyi, T.-S. Wei, J.-W. Hong, W. Lin, and Y.-K. Tu, "High Performance InGaAs MSM Photodetectors", The First International Symposium on Lasers and Optoelectronics Technology & Applications, Singapore, 1993.
12. Y. J. Chan, J.-I. Chyi, C. S. Wu, H.-P. Hwang, M. T. Yang, R.-M. Lin, and J.-L. Shieh, "In_{0.29}Al_{0.71}As/In_{0.3}Ga_{0.7} Heterostructure Devices Grown on GaAs Substrates with a Metamorphic Buffer Design", 1994 Device Research Conf., Boulder, Colorado, U.S.A. 1994.
13. J.-I. Chyi, R.-J. Lin, R.-M. Lin, J.-L. Shieh, and J.-W. Pan, "Schottky Barrier Heights of In_xAl_{1-x}As (0<x<0.35) Epilayers on GaAs", 1994 Intl. Conf. Solid State Devices and Materials, Yokohama, Japan, 1994.
14. J.-W. Pan, J.-L. Shieh, J.-H. Gau, J.-I. Chyi, J.-C. Lee, and K.-J. Ling, "The Study of the Optical Properties of In(Al_xGa_{1-x})As by Variable Angle Spectroscopic Ellipsometry", 7th Intl. Conference on InP and Related Materials, Sapporo, Hokkaido, Japan, 1995.
15. C.-S. Wu, Y.-J. Chan, T.-H. Gan, J.-L. Shieh, and J.-I. Chyi, "In(Al_{0.9}Ga_{0.1})As/InGaAs HEMTs on InP Substrates", 7th Intl. Conference on InP and Related Materials, Sapporo, Hokkaido, Japan, 1995.
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18. J.-I. Chyi, J.-H. Gau, J.-L. Shieh, J.-W. Pan, Y.-J. Chan, C. C. Chang, and F. Y. Chuang, "Characteristics of InAlGaAs/AlGaAs Strained Quantum Well Lasers Grown by MBE", The 1994 IUMRS Intl. Conf. on Electron. Materials, Hsinchu, Taiwan, R.O.C. 1994.
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22. J.-L. Shieh, J.-I. Chyi, R.-M. Lin, and J.-W. Pan, "Residual Strain and Crystallographic Tilt of In_xGa_{1-x}As and In_xAl_{1-x}As (0<x<0.3) Epilayers Grown on GaAs Substrates", 22nd Intl. Sym. on Compound Semiconductors", Cheju Island, Korea, 1995.

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34. T.-E. Nee, N.-T. Yeh, J.-I. Chyi, and C.-T. Lee, "Matrix-Dependent Structural and Photoluminescence Properties of $\text{In}_{0.5}\text{Ga}_{0.5}\text{As}$ Quantum Dots Grown by Molecular Beam Epitaxy", Intl. Workshop on Nano-Physics and Electronics, Tokyo, Japan, 1997.
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